



EEPROM VS FLASH MEMORY

| EEPROM | VS | FLASH MEMORY |
|--|--------------------------------------|---|
| ✓ | Non volatile memory | ✓ |
| ✗ | Write / erase cycles less than 100k | ✓ |
| ✓ | Write / erase cycles up to 1 million | ✗ |
| ✗ | Data retention more than 10 years | ✓ |
| ✗ | Block erase | ✓ |
| ✓ | Bit level erase | ✗ |
| ✗ | Large storage capacity | ✓ |
| ✗ | Faster write cycles | ✓ |
| ✗ | Faster erase cycles | ✓ |
| ✓ | Lower overall power use | ✗ |
| Memory access is random. Read is faster | Faster read cycles | Memory access is sequential. Read is slower. |
| Nor | NAND or NOR Gates | NAND |
| Faster as the architecture is based on NOR | Access to this memory | Slower as the architecture is based on NAND |
| Less compared to flash memory | Memory density | More compared to EEPROM |
| Mainly used in applications to store configuration data | Applications | Mainly used for program storage and data storage |
| More endurance than flash memory | Endurance | Less endurance than EEPROM |
| Range size from KB to MB | Size of the range | Range size up to GB |